



1-Channel USB3.1 GEN-2 ReDriver

Features

- → 5 & 10Gbps serial link with linear equalizer.
- → USB3.1 and USB3.0 Compatible
- → Full Compliancy to USB3.1 Super Speed Standard
- → Single 10Gbps differential signal pairs
- → Pin Adjustable Receiver Equalization
- → Pin Adjustable Flat Gain
- → 100 Ω Differential CML I/O's
- → Automatic Receiver Detect
- → Auto "Slumber" mode for adaptive power management
- → Single Supply Voltage: 3.3V
- → Packaging:
 - ◆ 18-pin, X2QFN 2x2 mm (XUA18)

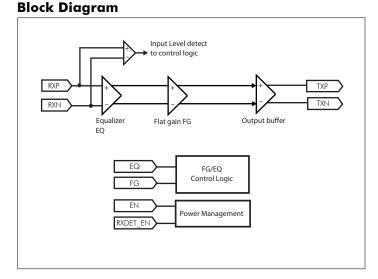
Description

The PI3EQX1001 is a low power, high performance 10.0 Gbps 1-Channel USB 3.1 linear ReDriver[™] designed specifically for the USB 3.1 protocol.

The device provides programmable equalization, and flat gain to optimize performance over a variety of physical mediums by reducing Inter-Symbol Interference. PI3EQX1001 supports one 100Ω Differential CML data I/O's between the Protocol ASIC to a switch fabric, over cable, or to extend the signals across other distant data pathways on the user's platform.

The integrated equalization circuitry provides flexibility with signal integrity of the signal before the ReDriver. The channels' input signal level determines whether the output is active.

The PI3EQX1001 also includes an automatic receiver detect function. The receiver detection loop will be active again if the corresponding channel's signal detector is idle for longer than 7.3mS. The channel will then move to Unplug Mode if load not detected, or it will return to Low Power Mode (Slumber Mode) due to inactivity.



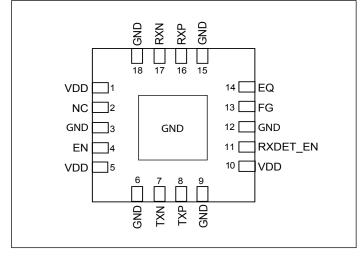
Pericom PC Monito USB 3.1ReDriver Pericom USB 3.1ReDriver Tablet PC **External Storag**

Figure1





Pin Diagram (18-pin, X2QFN 2x2mm) XUA18



Pin Description

Pin #	Pin Name	Туре	Description	
1, 5, 10	VDD	Power	3.3V power supply, +/-0.3V	
13	FG	Input	The DC flat gain selection. 4-level input pins. With internal 100K Ω pull-up resistor and 200k Ω pull-down resistor.	
14	EQ	Input	The EQ selection. 4-level input pins. With internal 100K Ω pull-up resistor and 200k Ω pull-down resistor.	
16, 17	RXP, RXN	Input	CML input terminals. With selectable input termination between 50 Ω to VDD, 67k Ω to VbiasRx or 67k Ω to GND.	
8,7	TXP, TXN	Output	CML output terminals. With selectable output termination between 50 Ω to VDD 4K to VDD, 4K to VbiasTx or Hi-Z	
			Receiver detection Enable pin. With internal 300 k Ω pull-up resistor.	
11	RXDET_EN	Input	"High" – Receiver detection is enabled.	
			"Low" – Receiver detection is disabled.	
			Channel Enable. With internal 300 k Ω pull-up resistor.	
4	EN	Input	"High" – Channel is in normal operation.	
			"Low" – Channel is in power down mode.	
3, 6, 9, 12, 15, 18, Center Pad	GND	GND	Supply Ground	
2	NC	NC	No Connect	





Power Management

Notebooks, netbooks, and other power sensitive consumer devices require judicious use of power in order to maximize battery life. In order to minimize the power consumption of our devices, Diodes has added an additional adaptive power management feature. When a signal detector is idle for longer than 1.3ms, the corresponding channel will move to low power mode ONLY. (It means both channels will move to low power mode individually).

In the low power mode, the signal detector will still be monitoring the input channel. If a channel is in low power mode and the input signal is detected, the corresponding channel will wake-up immediately. If a channel is in low power mode and the signal detector is idle longer than 6ms, the receiver detection loop will be active again. If load is not detected, then the Channel will move to Device Unplug Mode and monitor the load continuously. If load is detected, it will return to Low Power Mode and receiver detection will be active again per 6ms.

Operating Modes

Mode	R _{IN}	R _{OUT}
PD	$67 \mathrm{K}\Omega$ to GND	HIZ
Unplug Mode	$67 \mathrm{K}\Omega$ to VbiasRx	4KΩ to VbiasTx
Deep Slumber Mode	50Ω to Vdd	4KΩ to VbiasTx
Slumber Mode	50Ω to Vdd	4KΩ to Vdd
Active Mode	50Ω to Vdd	50Ω to Vdd



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PI3EQX1001

Equalization Setting:

EQ is the selection pin for the equalization selection

Ed		setting (dB)
EQ	@2.5GHz	@5GHz
0 (Tie 0Ω to GND)	5.1	10.9
R (Tie Rext to Gnd)	1.9	6.7
F (Leave Open)	3.5	8.9 (Default)
1 (Tie 0Ω to VDD)	6.8	13.1

Flat Gain Setting:

FG is the selection pin for the DC gain

	Flat Gain Settings
FG	dB
0 (Tie 0Ω to GND)	-3
R (Tie Rext to Gnd)	-1.5
F (Leave Open)	0 (Default)
1 (Tie 0Ω to VDD)	+2

Channel Enable Setting:

EN is the channel enable pin

	Channel Enable Setting
EN	Setting
0	Disabled
1	Enabled (Default)

Receiver Detection Setting:

RXDET_EN is the receiver detection pin

	Receiver Detection Setting
RXDET_EN	Setting
0	Disabled
1	Enabled (Default)



Note:



PI3EQX1001

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

<u> </u>	
Storage Temperature	65°C to +150°C
Supply Voltage to Ground Potential	-0.5V to +4.6V
DC SIG Voltage	$-0.5V$ to $V_{DD} + 0.5V$
Output Current	25mA to +25mA
Power Dissipation Continuous	
ESD, Human Body Model	-2kV to +2kV

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Control pin Specifications (VDD = 3.3 ± 0.3 V TA = 0 to 70°C)

Symbol	Parameter	Min.	Тур.	Max.	Units
2-level control	pins				
V _{IH}	DC input logic High	VDD*0.65			V
V _{IL}	DC input logic Low			VDD*0.35	V
I _{IH}	Input High current			25	uA
I _{IL}	Input Low current	-25			uA
4-level control	pins				
V _{IH}	DC input logic "High"	0.92*VDD	VDD		V
V _{IF} DC input logic "Float"		0.59*VDD	0.67*VDD	0.75*VDD	V
V _{IR} DC input logic "With Rext to GND"		0.25*VDD	0.33*VDD	0.41*VDD	V
V _{IL} DC input logic "Low"			GND	0.08*VDD	V
I _{IH} Input High current				50	uA
I _{IL}	Input Low current	-50			uA
Rext	External resistor connects to GND (±5%)	64.6	68	71.4	kΩ

AC/DC Electrical Characteristics (VDD = 3.3 ± 0.3 V TA = 0 to 70°C)

Power and Latency						
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{dd-3.3}	Supply voltage		3.0	3.3	3.6	V
I _{active}	Active mode current consumption	EN=1 (VDD=3.3V, 10Gbps, compliance test pattern, _{RXDET_EN} =High)		65	88	mA
I _{slumber}	Slumber mode current consumption	EN=1 (VDD=3.3V, no input signal longer than T _{slumber} /RXDET_EN=High)		8	11	
I _{DeepSlumber}	Deep slumber mode current con- sumption	EN=1 (VDD=3.3V, no input signal longer than T _{DeepSlumber/ RXDET_EN} =High)		0.4	0.7	mA
Iunplug	Unplug mode current consumption	EN=1, no output load is detected		0.3	0.5	
I _{pd}	Power Down mode current con- sumption	EN=0		10	50	μA
t _{pd}	Latency	From input to output			2	ns





AC/DC Electrical Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
CML Receiver	r Input (100 Ω differential)					
Receiver Elect	rical Specification					
C _{rxparasitic}	The parasitic capacitor for RX				1.0	pF
R _{RX-DIFF-DC}	DC Differential Input Impedance		72		120	
R _{RX-SINGLE} _ DC	DC single ended input impedance	DC impedance limits are need to guar- antee RxDet. Measured with respect to GND over a voltage of 500mV max	18		30	Ω
Z _{RX-HIZ-DC-} PD	DC input CM input impedance for V>0 during reset or power down	(Vcm=0 to 500mV)	25			kΩ
Cac_coupling	AC coupling capacitance		75		265	nF
V _{RX-CM-AC-P}	Common mode peak voltage	AC up to 5GHz			150	mV- peak
$ \begin{array}{ c c c c c } \hline V_{RX-CM-DC-} & Common mode peak voltage \\ \hline Active-Idle- & Avg_{uo}(V_{TX-D+} + V_{TX-D-})/2 - Avg_{u1}(V_{TX-D+} \\ \hline Delta-P & + V_{TX-D-})/2 \end{array} $		Between U0 and U1. AC up to 5GHz			200	mV- peak
Transmitter E	lectrical Specification					
V _{TX-DIFF-PP}	Ouput differential p-p voltage swing	Differential Swing V _{TX-D+} -V _{TX-D-}			1.2	Vppd
R _{TX-DIFF-DC}	DC Differential TX Impedance		72		120	Ω
V _{TX-RCV-DET}	The amount of voltage change al- lowed during RxDet				600	mV
Cac_coupling	AC coupling capacitance		75		265	nF
T _{TX-} EYE(10Gbps)	Transmitter eye, Include all jittter	At the silicon pad. 10Gbps	0.646			UI
T _{TX-} EYE(5Gbps) Transmitter eye, Include all jittter		At the silicon pad. 5Gbps	0.625			UI
T _{TX-DJ-} DD(10Gbps)	Transmitter deterministic jittter	At the silicon pad. 10Gbps			0.17	UI
T _{TX-DJ-} DD(5Gbps)	Transmitter deterministic jittter	At the silicon pad. 5Gbps			0.205	UI
C _{txparasitic}	The parasitic capacitor for TX				1.1	pF
R _{TX-DC-CM}	Common mode DC output Imped- ance		18		30	Ω
V _{TX} -DC-CM	The instantaneous allowed DC com- mon mode voltage at the connector side of the AC coupling capacitors	$ V_{TX-D+}+V_{TX-D-} /2$	0		2.2	V
V _{TX-C}	Common-Mode Voltage	$ V_{TX-D+}+V_{TX-D-} /2$	VDD- 1.5V		VDD	V
V _{TX-CM-AC-} PP-Active	Active mode TX AC common mode voltage	$V_{TX\text{-}D\text{+}}\text{+}V_{TX\text{-}D\text{-}}$ for both time and amplitude			100	mVpp





AC/DC Electrical Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{TX-CM-DC-} Active_Idle- Delta	Common mode delta voltage Avg _{uo} (V _{TEX-D+} + V _{TX-D-}])/2-Avg _{u1} (V _{TX-D+} + V _{TX-D-}])/2	Between U0 to U1			200	mV- peak
V _{TX} -Idle-Diff- AC-pp	Idle mode AC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between Tx+ and Tx- in idle mode. Use the HPF to remove DC components. =1/ LPF. No AC and DC signals are applied to Rx terminals.			10	mVppd
V _{TX} -Idle-Diff- DC	Idle mode DC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between Tx+ and Tx- in idle mode. Use the LPF to remove DC components. =1/ HPF. No AC and DC signals are applied to Rx terminals.			10	mV
Channel Perfo	ormance					
G _p	Peaking gain (Compensation at 5GHz, relative to 100MHz, 100mV _p . _p sine wave input, FG=F)	EQ=0 EQ=R EQ=F EQ=1		10.9 6.7 8.9 13.1		dB
		Variation around typical	-3		+3	dB
G _F	Flat gain (100MHz, EQ=F)	FG=0 FG=R FG=F FG=1		-3 -1.5 0 +2		dB
V _{SW_100M}	-1dB compression point output swing (at 100MHz)	Variation around typical	-3	1000	+3	dB mVppd
V _{SW_5G}	-1dB compression point output swing (at 5GHz)			750		mVppd
V _{noise-input}	Input-referred noise	100MHz to 5GHz, FG=1, EQ=R, Figure 2 100MHz to 5GHz, FG=1, EQ=1, Figure 2		0.6		mV _{RMS}
V _{noise-output}	Output-referred noise ¹	100MHz to 5GHz, FG=1, EQ=R, Figure 2 100MHz to 5GHz, FG=1, EQ=1, Figure 2		0.8		mV _{RMS}
Signal and Fre	equency Detectors					
V _{th_upm}	Unplug mode detector threshold	Threshold of LFPS when the input imped- ance of the redriver is 67kohm to Vbi- asRx only. Used in the unplug mode.	200		800	mVppd
V _{th_dsm}	Deep slumber mode detector threshold	LFPS signal threshold in Deep slumber mode	100		600	mVppd
V _{th_am}	Active mode detector threshold	Signal threshold in Active and slumber mode	45		175	mVppd
F _{th}	LFPS frequency detector	Detect the frequency of the input CLK pattern	100		400	MHz

Note: 1. Guaranteed by design and characterization.





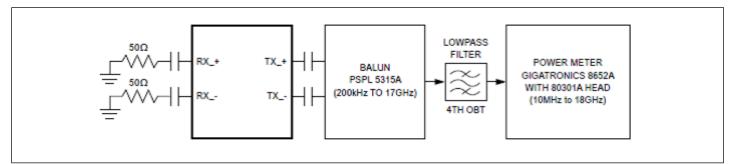


Figure2. Noise test configuration

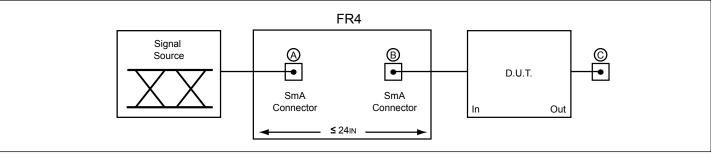
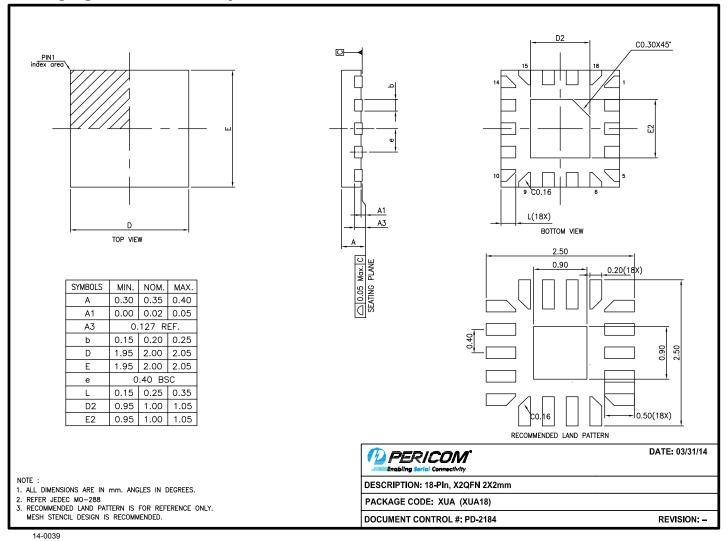


Figure3. Test Condition Referenced in the Electrical Characteristic Table





Packaging Mechanical: 18-pin X2QFN



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Number	Package Code	Package Description
PI3EQX1001XUAEX	XUA	18-Pin, 2X2mm (X2QFN)

Notes:

· Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/

• E = Pb-free and Green

• X suffix = Tape/Reel





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